

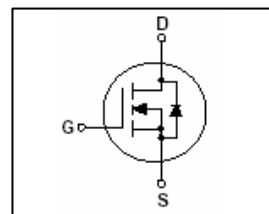
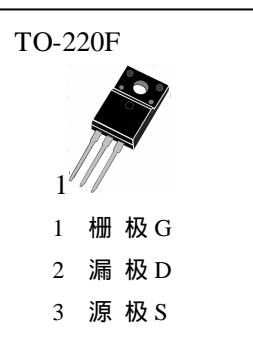


汕头华汕电子器件有限公司

N-Channel Enhancement Mode Field Effect Transistor

HFF2N60对应国外型号
SSS2N60B**主要用途**

高速开关应用。

极限值 (T_a=25 °C)T_{stg}——贮存温度..... -55~150T_j——结温..... 150V_{DSS}——漏极—源极电压..... 600VV_{GS}——栅极—源极电压..... ±30VI_D——漏极电流 (T_c=25 °C) 2.0AP_D——耗散功率 (T_c=25 °C) 23W**电参数 (T_a=25 °C)****外形图及引脚排列**

参数符号	符 号 说 明	最 小 值	典 型 值	最大 值	单 位	测 试 条 件
BV _{DSS}	漏—源极击穿电压	600			V	I _D =250 μA, V _{GS} =0V
I _{DSS}	零栅压漏极电流		10	μA		V _{DS} =600V, V _{GS} =0
I _{GSS}	栅极泄漏电流		± 100	nA		V _{GS} =±30V, V _{DS} =0V
V _{GS(th)}	栅—源极开启电压	2.0		4.0	V	V _{DS} =V _{GS} , I _D =250 μA
R _{DS(on)}	漏—源极导通电阻		3.8	5.0	?	V _{GS} =10V, I _D =1.0A
g _{fs}	正向跨导		2.05		S	V _{DS} =40V, I _D =1.0A
C _{iss}	输入电容	180	235	pF		V _{DS} =25V, V _{GS} =0, f=1MHz
C _{oss}	输出电容	20	25	pF		
C _{rss}	反向传输电容	4.3	3	pF		
t _{d(on)}	导通延迟时间	9	28	nS		V _{DD} =300V, I _D =2A (峰值) R _G =25
t _r	上升时间	25	60	nS		
t _{d(off)}	断开延迟时间	24	58	nS		
t _f	下降时间	28	66	nS		V _{DS} =480V V _{GS} =10V I _D =2A
Q _g	栅极总电荷	8.5	12	nC		
Q _{gs}	栅极—源极电荷	1.3		nC		
Q _{gd}	栅极—漏极电荷	4.1		nC		I _S =2.0A, V _{GS} =0 结到外壳
I _s	源极—漏极二极管正向电流		2.0	A		
V _{SD}	源极—漏极二极管导通电压		1.4	V		
R _{th(j-c)}	热阻		5.5	/W		

*注：脉冲测试，宽度 300 μS, 占空比 2%



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特性曲线

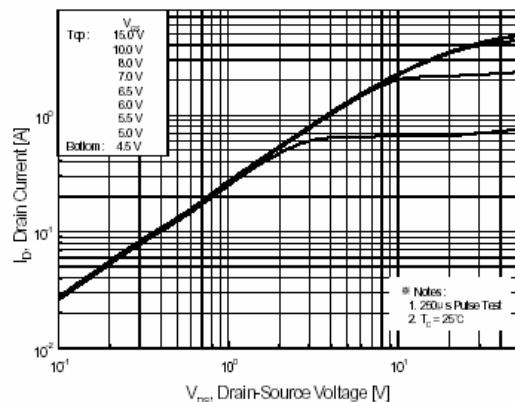


Figure 1. On-Region Characteristics

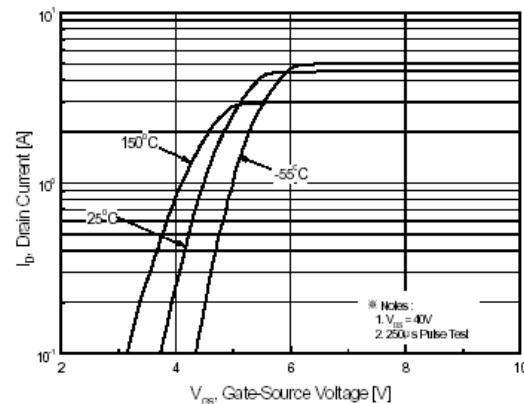


Figure 2. Transfer Characteristics

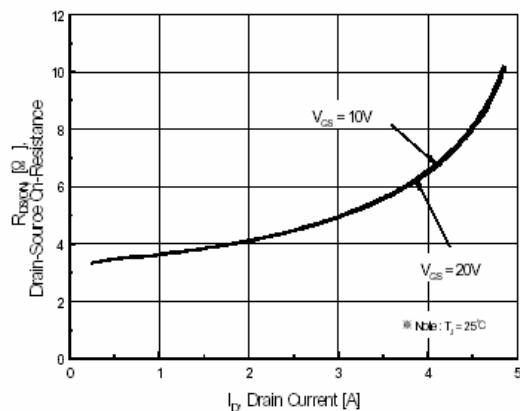


Figure 3. On-Resistance Variation vs
Drain Current and Gate Voltage

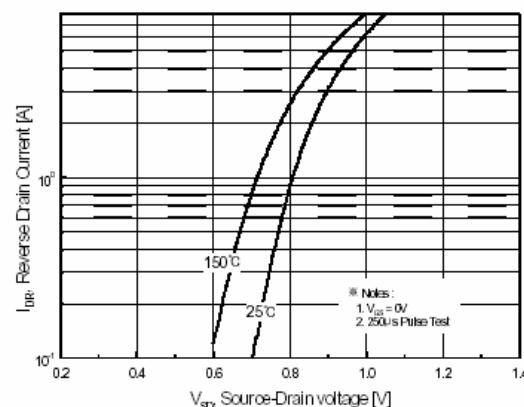


Figure 4. Body Diode Forward Voltage
Variation with Source Current
and Temperature

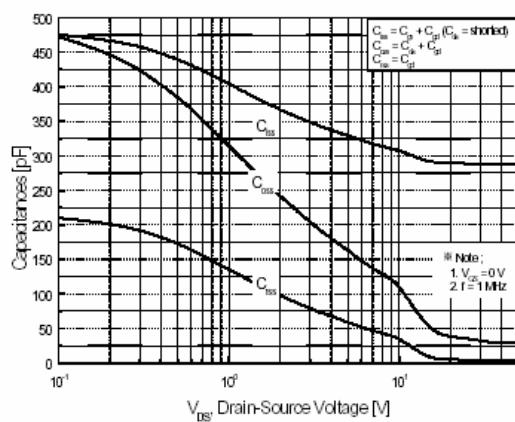


Figure 5. Capacitance Characteristics

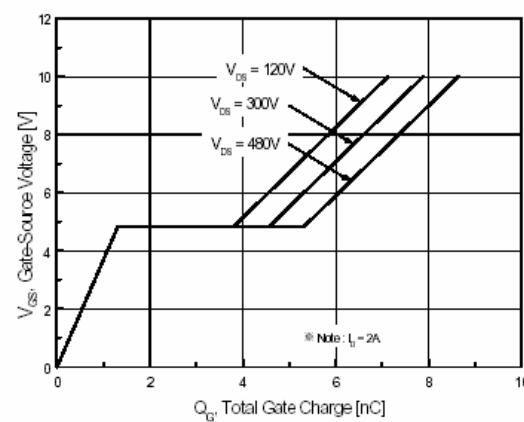


Figure 6. Gate Charge Characteristics



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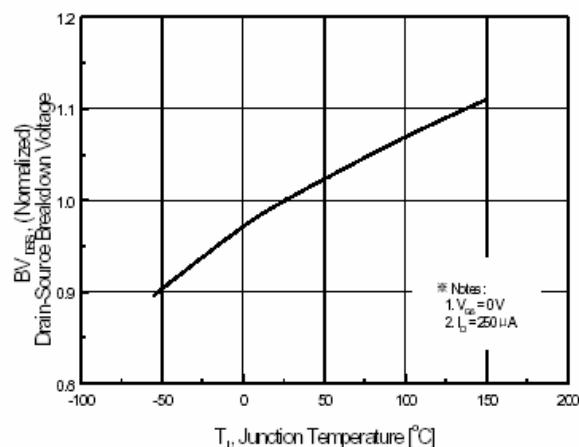


Figure 7. Breakdown Voltage Variation
vs Temperature

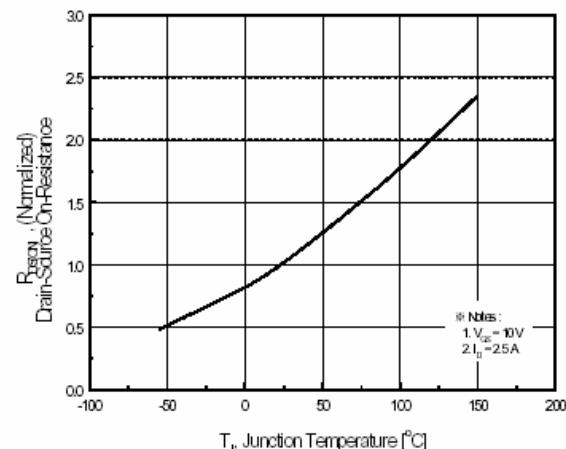


Figure 8. On-Resistance Variation
vs Temperature

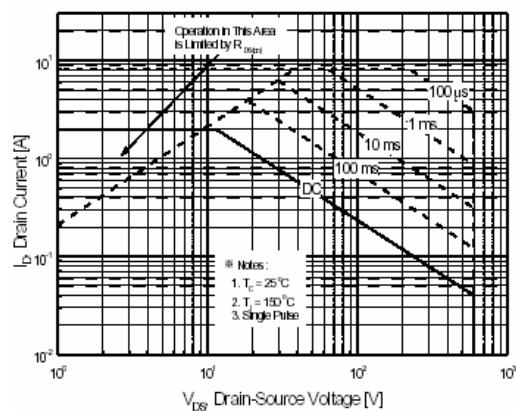


Figure 9-2. Maximum Safe Operating Area
for HFF2N60

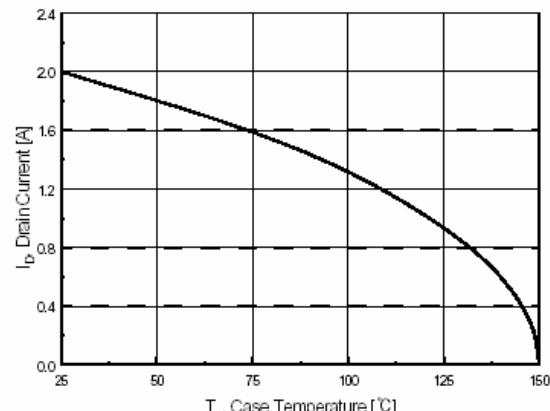


Figure 10. Maximum Drain Current
vs Case Temperature

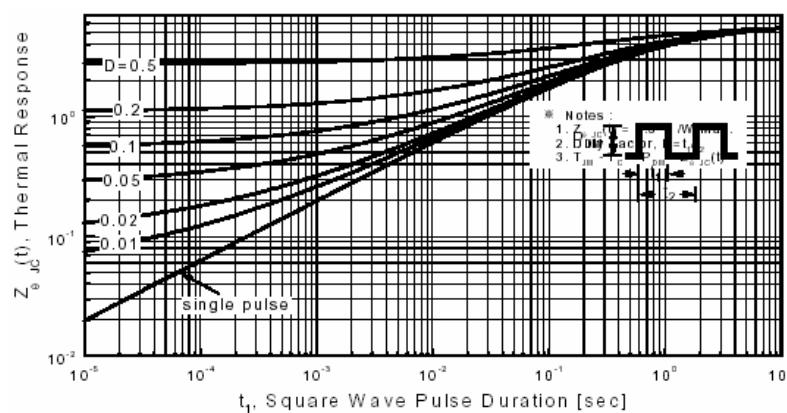


Figure 11-2. Transient Thermal Response Curve for HFF2N60



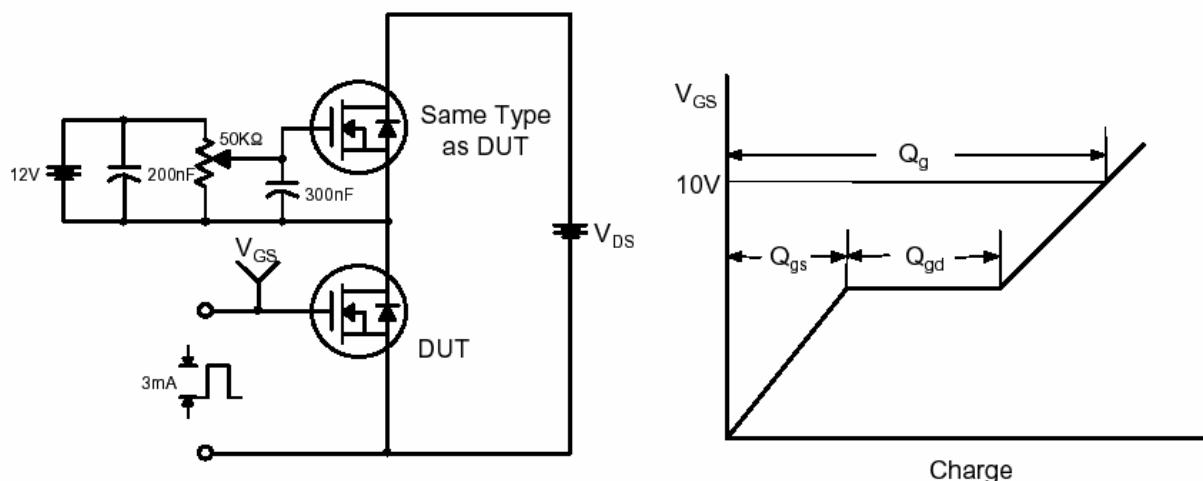
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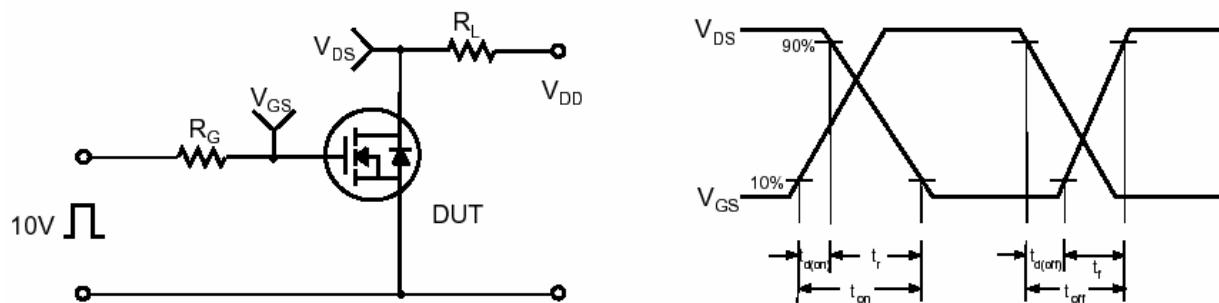
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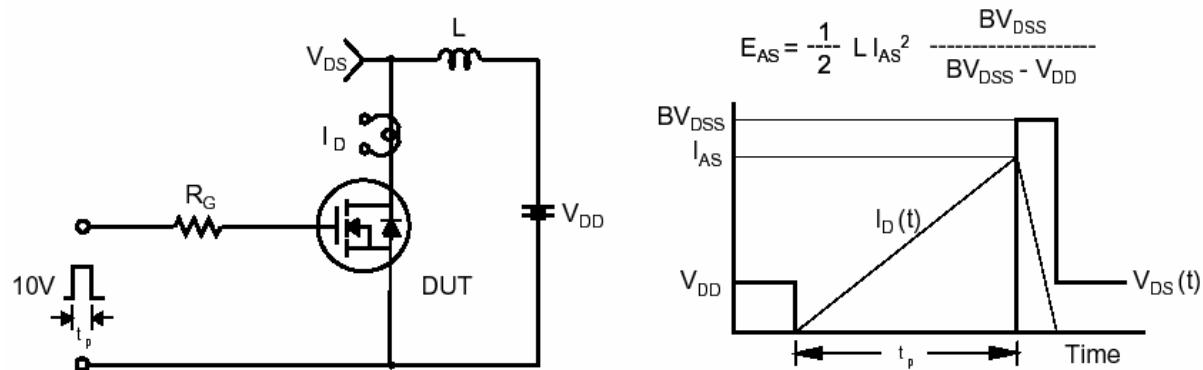
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms





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N-Channel Enhancement Mode Field Effect Transistor

HFF2N60

对应国外型号
SSS2N60B

Peak Diode Recovery dv/dt Test Circuit & Waveforms

